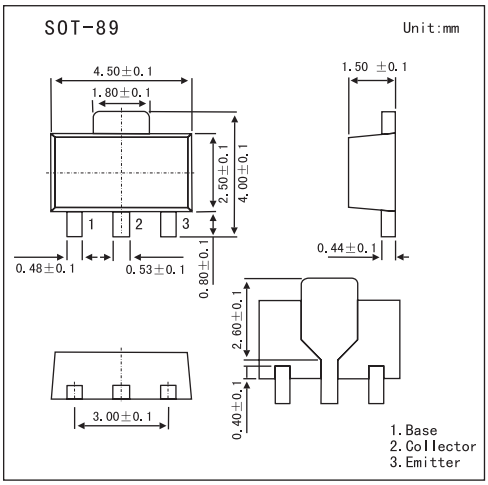
Low VCE(sat) Transistor

2SB1424



■ Features

- Low $V_{CE(sat)}$. $V_{CE(sat)}$ = -0.2V (Typ.) (I_C/I_B = -2A / -0.1A)
- Excellent DC current gain characteristics.
- PNP silicon transistor

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-20	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_C	-3	A
	I_{CP} *	-5	A
Collector dissipation	P_C	0.5	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* Single pulse Pw=10ms.

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltae	V_{CBO}	I_C= -50μA	-20			V
Collector-emitter breakdown voltage	V_{CEO}	I_C= -1mA	-20			V
Emitter-base breakdown voltage	V_{EBO}	I_E= -50μA	-6			V
Collector cutoff current	I_{CBO}	V_{CB}= -20V			-0.1	μA
Emitter cutoff current	I_{EBO}	V_{EB}= -5V			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-2V, I_C= -0.1A	120		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C/I_B= -2A/ -0.1A			-0.5	V
Output capacitance	C_{ob}	V_{CB}= -10V, I_E=0A, f=1MHz		35		pF
Transition frequency	f_T	V_{CE}= -2V, I_E=0.5A, f=100MHz		240		MHz

■ h_{FE} Classification

Marking	AEQ	AER
Rank	Q	R
hFE	120～270	180～390